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<b>FORM PTO-1449</b> <b>INFORMATION DISCLOSURE STATEMENT</b>		Atty. Docket		Application No.	
		SUND 466		10/603,659	
		Applicant			
		Mu-Jen LAI et al.			
		Filing Date		Group	
		June 26, 2003		2814	
<b>U.S. PATENT DOCUMENTS</b>					
Examiner Initial		Document Number	Date	Name	Class
	AA				
	AB				
	AC				
	AD				
	AE				
	AF				
	AG				
	AH				
<b>FOREIGN PATENT DOCUMENTS</b>					
		Document Number	Date	Country	Class
	AJ				
	AJ				
	AK				
	AL				
<b>OTHER (Including Author, Title, Date, Pertinent Pages, etc.)</b>					
	AM	"ZnTe-GaN heterostructure switching device", A. G. Drizhuk et al.; Tech. Phys. Lett. 23 (10), October 1997; 1997 American Institute of Physics; pages 809 and 810			
	AN	"Growth of GaN on Si substrates - roles of BP thin layer" Optical Materials, S. Nishimura et al., one page - ISI Web of Science 6-0			
Examiner <i>M. J. Lai</i>					Date Considered 8-17-04
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.					